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### Silicon Epitaxial Planar Zener Diode for Surge Absorb



ADE-208-1458A (Z)

Rev.1 Nov. 2002

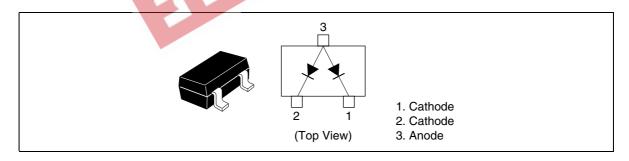
#### **Features**

- HZM3.3WA has two devices, and can absorb surge.
- MPAK Package is suitable for high density surface mounting.

### **Ordering Information**

| <ul> <li>MPAK Package is suitable for</li> </ul> | 2          |              |
|--|------------|--------------|
| Ordering Information                             |            | A TE ST CIT  |
| Type No.   | Laser Mark | Package Code |
| HZM3.3WA   | 33A        | MPAK         |

### Pin Arrangement



### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

| Item                 | Symbol | Value       | Unit |
|----------------------|--------|-------------|------|
| Power dissipation    | Pd *1  | 200         | mW   |
| Junction temperature | Tj     | 150         | °C   |
| Storage temperature  | Tstg   | -55 to +150 | °C   |

Note 1. Two device total, See Fig.2.

### **Electrical Characteristics** \*1

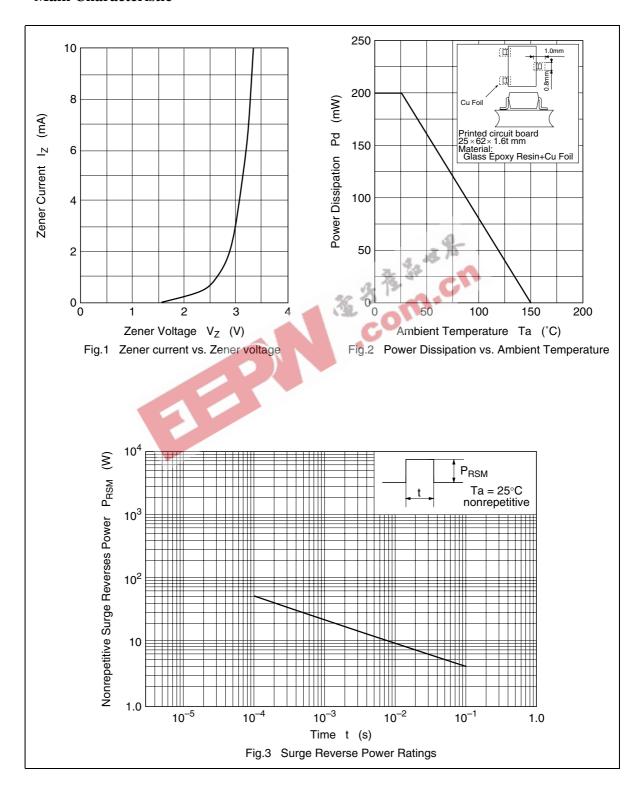
 $(Ta = 25^{\circ}C)$ 

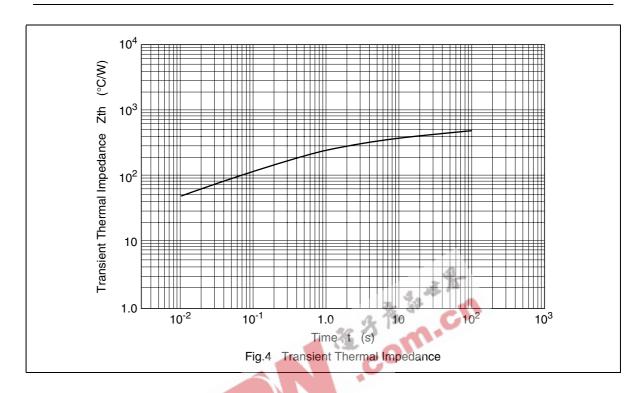
| Item               | Symbol         | Min  | Тур | Max  | Unit Test Condition   |
|--------------------|----------------|------|-----|------|---|
| Zener voltage      | $V_z$          | 3.10 | _   | 3.50 | V $I_z = 5 \text{ mA, } 40 \text{ ms pulse}$  |
| Reverse current    | I <sub>R</sub> | _    | _   | 20   | μΑ V <sub>R</sub> = 1.0 V   |
| Dynamic resistance | r <sub>d</sub> | _    |     | 130  | $\Omega$ $I_z = 5 \text{ mA}$   |
| ESD-Capability *2  | _              | 30   |     |      | kV $C = 150 \text{ pF}, R = 330 \Omega$ , Both forward and reverse direction 10 pulse |

Notes: 1. Per one device.

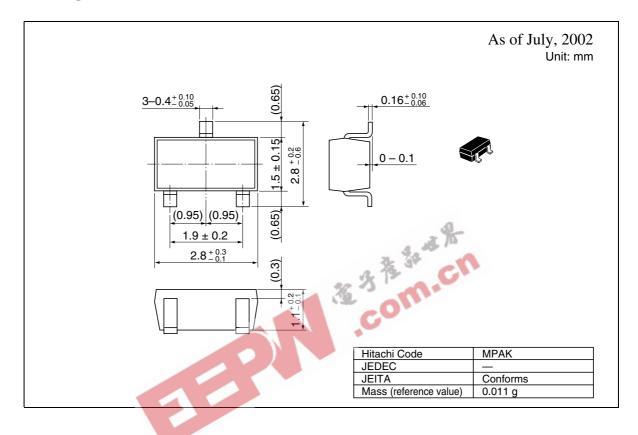
2. Failure criterion ;  $I_{\scriptscriptstyle R}$  > 20  $\mu A$  at  $V_{\scriptscriptstyle R}$  = 1.0 V.

### **Main Characteristic**





### **Package Dimensions**



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